


Received: 4-2-04

FORM PTO-1449				ATTY DOCKET NO.		SERIAL NO.	
INFORMATION DISCLOSURE STATEMENT				51898		10/816,356 Not Yet Assigned	
				APPLICANT(S): Woelk et al.			
				FILING DATE: Herewith 04/02/2004		ART UNIT: 2813 Not Yet Assigned	
UNITED STATES PATENT DOCUMENTS							
EXAM. INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FIL. DATE IF APPR
S.W.S.	AA	2,444,270	06/29/1948	E. Rochow	—	—	
S.W.S.	AB	3,446,824	05/27/1969	K. Moedritzer	—	—	
S.W.S.	AC	4,506,815	03/26/1985	Melas et al.	—	—	
S.W.S.	AD	3,470,220	09/30/1969	Moedritzer et al.	—	—	
S.W.S.	AE	5,120,394	06/09/1992	Mukai	—	—	
S.W.S.	AF	5,502,227	03/26/1996	Kanjolia et al.	—	—	
S.W.S.	AG	5,755,885	05/26/1998	Mikoshiha et al.	—	—	
S.W.S.	AH	6,099,903	08/08/2000	Kaloyeros et al.	—	—	
S.W.S.	AI	6,214,729	04/10/2001	Uhlenbrock et al.	—	—	
S.W.S.	AJ	6,238,734	05/29/2001	Senzaki et al.	—	—	
S.W.S.	AK	6,306,217	10/23/2001	Uhlenbrock et al.	—	—	
S.W.S.	AL	6,391,803	05/21/2002	Kim et al.	—	—	
S.W.S.	AM	6,444,038	09/03/2002	Rangarajan et al.	—	—	
S.W.S.	AN	6,444,041	09/03/2002	Vaartstra	—	—	
S.W.S.	AO	6,444,818	09/03/2002	Uhlenbrock et al.	—	—	
S.W.S.	AP	6,492,711	12/10/2002	Takagi et al.	—	—	
S.W.S.	AQ	6,509,587	01/21/2003	Sugiyama et al.	—	—	
S.W.S.	AR	6,514,886	02/04/2003	U'Ren	—	—	
S.W.S.	AS	2003/0082300	05/01/2003	Todd et al.	—	—	
S.W.S.	AT	2003/0111013	06/19/2003	Oosterlaken et al.	—	—	
Examiner: Stephen W. Smoot				Date: February 20, 2006			

Received: 4-2-04

Sheet 2 of 2

FORM PTO-1449		ATTY DOCKET NO. 51898		SERIAL NO. 10/816,536 Not Yet Assigned		
INFORMATION DISCLOSURE STATEMENT		APPLICANT(S): Woelk et al.				
		FILING DATE: Herewith 04/02/2004		ART UNIT: 2813 Not Yet Assigned		
FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS SUB CLASS	TRAN YES/NO
	BA	626,398	04/15/1946	United Kingdom		
S.W.S.	BB	1 160 355 A2	12/05/2001	Europe		
OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)						
S.W.S.	CA	Dittmar et al., Cyclopentadienyl Germanes as Novel Precursors for the CVD of Thin Germanium Films, Chem. Vap. Deposition 2001, 7, No. 5, pp. 193-195.				
S.W.S.	CB	Harrison et al., "Predeposition Chemistry Underlying the Formation of Germanium Films by CVD of Tetravinylgermane", Chem. Mater. 1994, 6, pp. 1620-1626.				
S.W.S.	CC	Hoffman et al., "Plasma-enhanced chemical vapor deposition of silicon, germanium, and tin nitride thin films from metalorganic precursors", J. Vac. Sci. Technol. A 13(3), May/Jun 1995, pp. 820-825.				
S.W.S.	CD	O. Johnson, "The Germanes and Their Organo Derivatives", Chem. Rev. 1951, 48, 259, pp. 259-297.				
S.W.S.	CE	Kidd et al., "Germanium-73 Nuclear Magnetic Resonance Spectra of Germanium Tetrahalides", Journal of American Chemical Society, 95:1, January 10, 1973, pp. 88-90.				
S.W.S.	CF	H. Ohshima, "Organo-germanium adsorption on a silicon surface by excimer light irradiation", Applied Surface Science 107 (1996) pp. 85-89.				
S.W.S.	CG	Bottei et al., "Organogermanium Chemistry", Chem. Rev. (1951), 48, 259, pp. 403-442.				
S.W.S.	CH	Sulkes et al., "Molecular beam study of possible CVD intermediates from Group-14 organometallic precursors", Chemical Physics Letters 318 (2000) pp. 448-453.				
S.W.S.	CI	D. Smith, "Structural Properties of heteroepitaxial germanium-carbon alloys grown on Si (100); Philosophical Magazine A, 2001, Vol. 81, No. 6, pp. 1613-1624.				
S.W.S.	CJ	Todd et al., "Influence on Precursor Chemistry on Synthesis of Silicon-Carbon Germanium Alloys", Mat. Res. Soc. Symp. Proc. Vol. 377, 1995, pp. 529-534.				
Examiner:		Stephen W. Smoot		Date: February 20, 2006		

FORM PTO-1449				ATTY DOCKET NO.		SERIAL NO.	
INFORMATION DISCLOSURE STATEMENT				51898		10/816,356	
				APPLICANT(S): Shenai-Khatkhate et al.			
				FILING DATE:		ART UNIT:	
				04/02/2004		2812	
UNITED STATES PATENT DOCUMENTS							
EXAM. INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILE DATE
S.W.S.	AA	3,935,040	01/27/1976	Mason	—	—	
S.W.S.	AB	3,985,590	10/12/1976	Mason	—	—	
S.W.S.	AC	4,720,561	01/19/1988	Bradley et al.	—	—	
S.W.S.	AD	4,812,586	03/14/1989	Mullin et al.	—	—	
S.W.S.	AE	5,316,958	05/31/1994	Meyerson	—	—	
S.W.S.	AF	5,489,550	02/06/1996	Moslehi	—	—	
S.W.S.	AG	2003/0230233 A1	12/18/2003	Fitzgerald et al.	—	—	
S.W.S.	AH	2004/0259333 A1	12/23/2004	Tomasini et al.	—	—	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRAN YES/NO
S.W.S.	BA	0 368 651 B1	09/07/1994	Europe	—	—	
S.W.S.	BB	1 386 900	03/12/1975	United Kingdom	—	—	
S.W.S.	BC	WO 2004/011473 A1	02/05/2004	International PCT	—	—	
OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)							
S.W.S.	CA	Dillon et al.; "Comparison of Trichlorosilane and Trichlorogermane Decomposition on Silicon Surfaces Using FTIR Spectroscopy"; Mat. Res. Soc. Symp. Proc. Vol. 282; 1993; pp. 405-411.					
S.W.S.	CB	Dillon et al.; "Adsorption and Decomposition of Diethylgermane on porous silicon surfaces"; Surface Science Letters 286 (1993); pp. L535-L541.					
S.W.S.	CC	Todd et al.; "Chemical Synthesis of Metastable Germanium-Carbon Alloys Grown Heteroepitaxially on (100) Si; Chem. Mater. 1996, 8, pp. 2491-2498.					
S.W.S.	CD	Coon et al.; "Germanium Deposition on Silicon: Surface Chemistry of (CH ₃ CH ₂) ₂ GeH ₂ and GeCl ₄ "; Mat. Res. Soc. Symp. Proc. Vol. 282; 1993; pp. 413-419.					
S.W.S.	CE	Kouvetakis et al.; "Novel Chemical Routes to Silicon-Germanium-Carbon Materials"; Appl. Phys. Lett. 65 (23); 5 December 1994; pp. 2960-2962.					
S.W.S.	CF	Dillon et al.; "Adsorption and Decomposition of Trichlorosilane and Trichlorogermane on Porous Silicon and Si(100)2x1 Surfaces"; J. Vac. Sci. Technol. A 13(1); Jan/Feb 1995; pp. 1-10.					
Examiner: <i>Stephen W. Smoot</i>				Date: February 20, 2006			